

Amendments to the Specification:

Please amend the specification as follows:

Please replace paragraph number [0001], with the following rewritten paragraph:

[0001] The present application is a continuation-in-part of U.S. Application Serial No. 10/389,456, filed by Wang et al. on March 14, 2003 and entitled "Shallow Trench Isolation for Strained Silicon Processes" (Attorney Docket No. 39153-638); U.S. Application Serial No. ~~10/341,683~~, 10/341,863 filed by Ngo et al. on ~~January 15, 2003~~ January 14, 2003 and entitled "Shallow Trench Isolation for Strained Silicon Processes" (Attorney Docket No. 39153-639); U.S. Application Serial No. 10/358,966, filed on February 5, 2003 by Lin et al. and entitled "Shallow Trench Isolation Process Using Oxide Deposition and Anneal for Strained Silicon Processes" (Attorney Docket No. 39153-648); and U.S. Application Serial No. 10/341,848, filed on ~~January 15, 2003~~ January 14, 2003 by Arasnia et al. and entitled "Post Trench Fill Oxidation Process for Strained Silicon Processes" (Attorney Docket No. 39153-645); all of which are assigned to the Assignee of the present application.